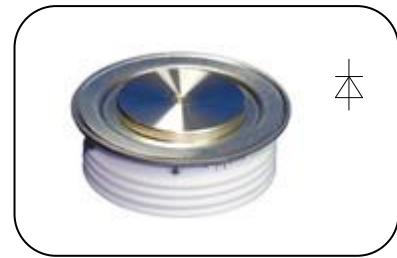


Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

I_{F(AV)}**1080A****V_{RRM}****1100~2000 V****I_{FSM}****9 kA****I²t****405 10³A²S****Typical Applications**

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Double side cooled,	T _C =85°C	175		1080	A
V _{RRM}	Repetitive peak reverse voltage	tp=10ms		175	1100	2000	V
I _{RRM}	Repetitive peak current	at V _{RRM}		175		30	mA
I _{FSM}	Surge forward current	10ms half sine wave V _R =0.6V _{RRM}	175			9	kA
I ² t	I ² t for fusing coordination					405	A ² s*10 ³
V _{FO}	Threshold voltage		175			0.98	V
r _F	Forward slope resistance					0.33	mΩ
V _{FM}	Peak forward voltage	I _{FM} =3770A, F=7.0kN	175			2.22	V
Q _{rr}	Recovery charge	I _{FM} =2000A, tp=2000μs, di/dt=-20A/μs, V _R =50V	175		1600		μC
R _{th(j-c)}	Thermal resistance Junction to case	DC double side cooled Clamping force 7.0kN				0.045	°C /W
R _{th(c-h)}	Thermal resistance case to heat sink					0.010	
F _m	Mounting force			5.3		10	kN
T _{stg}	Stored temperature			-40		175	°C
W _t	Weight				80		g
Outline		P33					

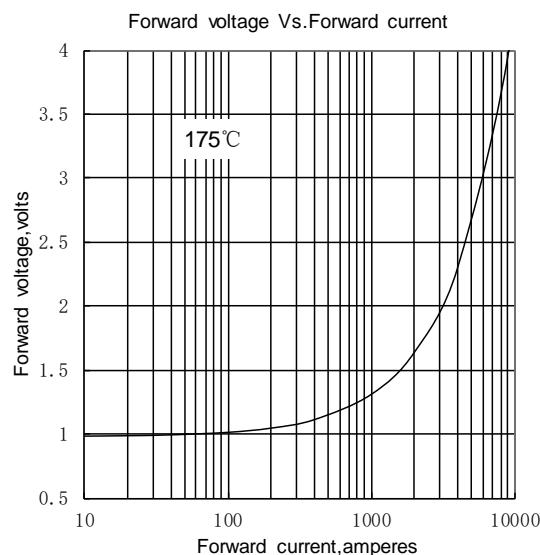


Fig.1

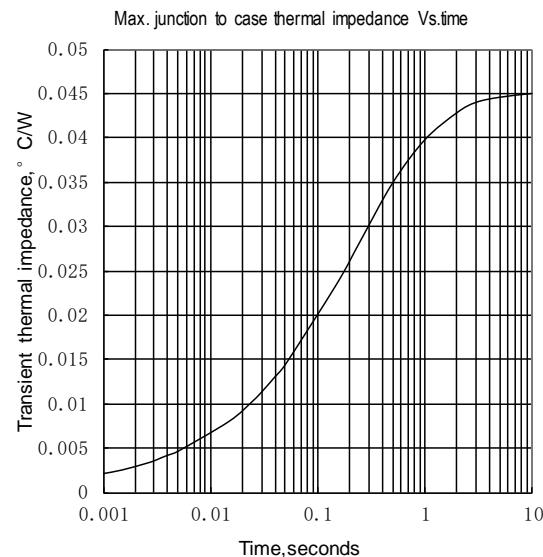


Fig.2

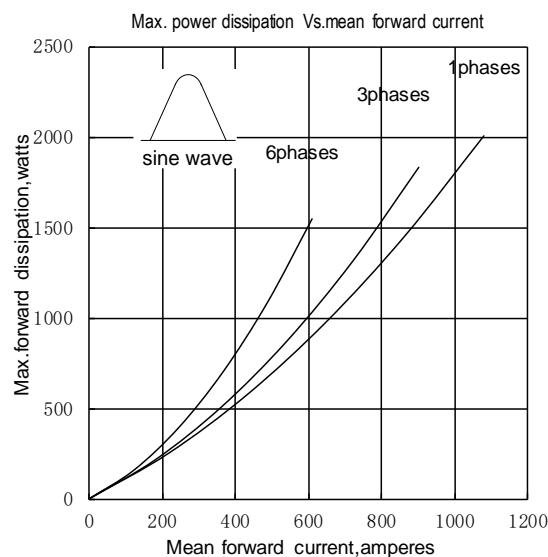


Fig.3

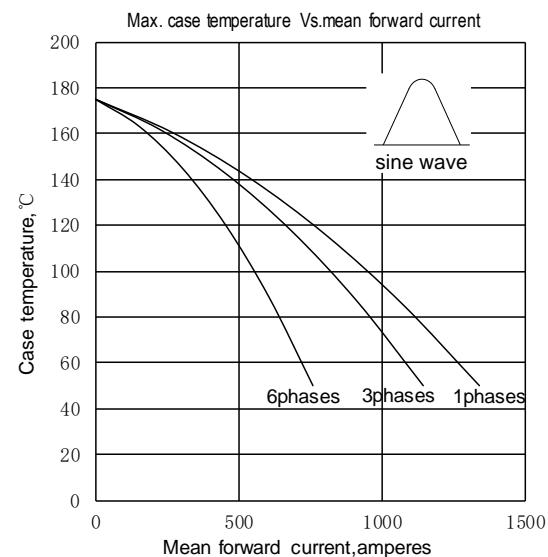


Fig.4

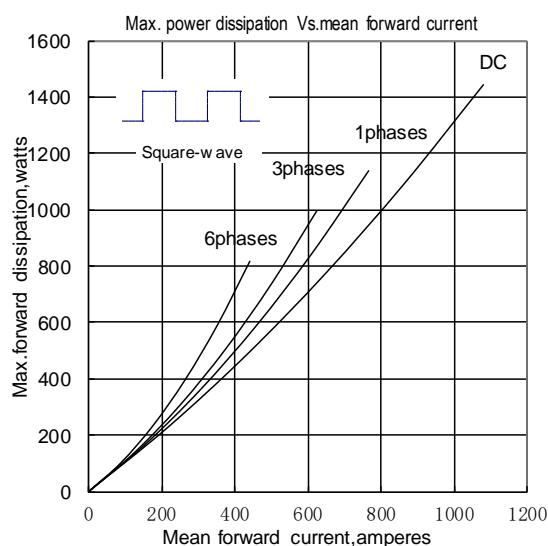


Fig.5

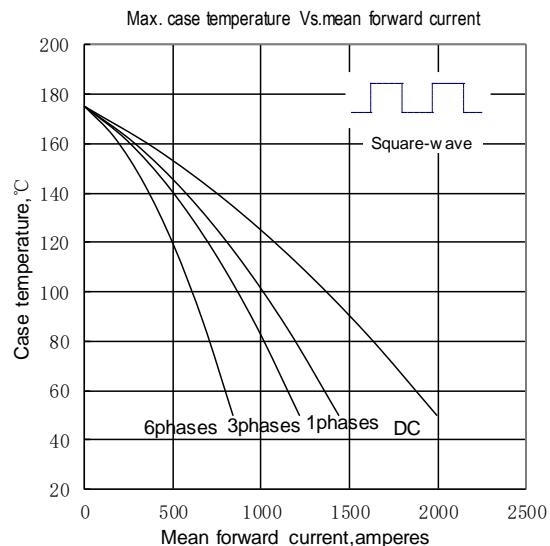


Fig.6

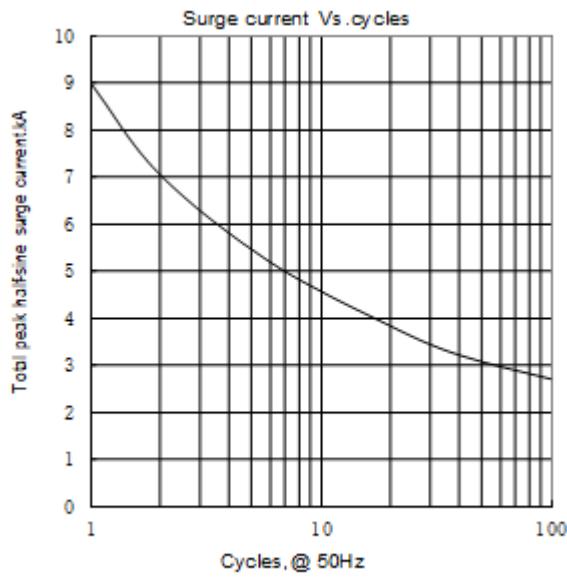


Fig.7

